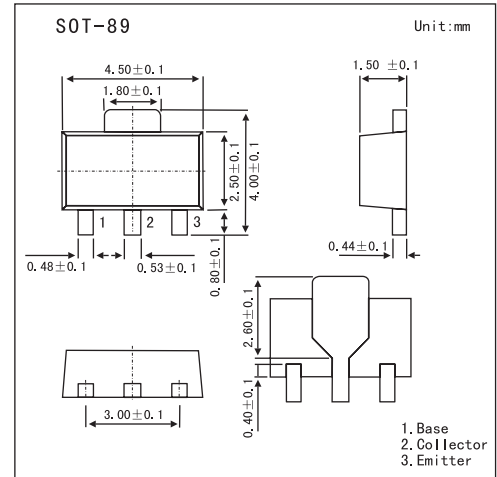


Silicon PNP Epitaxial

2SB1027



■ Features

- Low frequency amplifier

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	-180	V
Collector to emitter voltage	V _{CE0}	-160	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	I _C	-1.5	A
Collector peak current	i _{C(peak)} *1	-3	A
Collector power dissipation	P _C *2	1	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to 150	°C

*1 PW ≤ 10 ms, Duty cycle ≤ 20%

*2 Value on the alumina ceramic board (12.5X 20X 0.7 mm)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -1 mA, I _E = 0	-180			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -10 mA, R _{BE} = ∞	-120			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -1 mA, I _C = 0	-5			V
Collector cutoff current	I _{CBO}	V _{CB} = -160 V, I _E = 0			-10	μA
DC current transfer ratio	h _{FE}	V _{CE} = -5 V, I _C = -0.15 A,	60		320	
		V _{CE} = -5 V, I _C = -0.5 A,	30			
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -0.5 A, I _B = -50 mA,			-1.0	V
Base to emitter voltage	V _{BE}	V _{CE} = -5 V, I _C = -0.15 A,			-0.9	V

■ hFE Classification

Marking	EH	EJ	EK
hFE	60 to 120	100 to 200	160 to 320